

Application Specific Discretes
 A.S.D.™

PROGRAMMABLE TRANSIENT VOLTAGE SUPPRESSOR FOR SLIC PROTECTION

FEATURES

- DUAL PROGRAMMABLE TRANSIENT SUPPRESSOR
- HIGH SURGE CURRENT CAPABILITY.
 - $I_{PP} = 50A, 10/1000 \mu s$.
 - $I_{PP} = 60 A, 5/310 \mu s$.
 - $I_{PP} = 150 A, 2/10 \mu s$.
- HOLDING CURRENT = 150 mA min.
- LOW GATE TRIGGERING CURRENT :
 $I_{GT} = 15 mA$ max.

DESCRIPTION

This device has been especially designed to protect a subscriber line card interface (SLIC) against transient overvoltage.

Positive overloads are clipped with two diodes, while negative surges are suppressed by two protection thyristors, their breakdown voltage being is referenced to the -Vbat.

This component presents a very low gate triggering current (I_{GT}) in order to reduce the current consumption on the PC board during the firing phase.

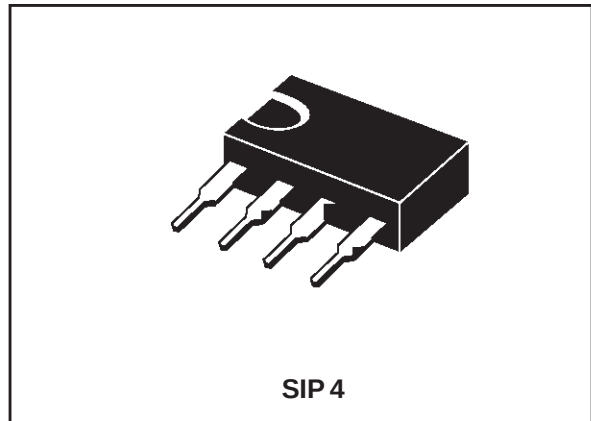
COMPLIES WITH THE FOLLOWING STANDARDS:

CCITT - K20	10/700 μs	1kV
	5/310 μs	25A
VDE 0433	10/700 μs	2kV
	5/200 μs	50A
VDE 0878	1.2/50 μs	1.5kV
	1/20 μs	40A
FCC part 68	2/10 μs	2.5kV
	2/10 μs	150A(*)
BELLCORE TR-NWT-001089 :	2/10 μs	2.5kV
	2/10 μs	150A(*)
	10/1000 μs	1kV
	10/1000 μs	50A(*)
CNET	0.5/700 μs	1kV
	0.2/310 μs	25A

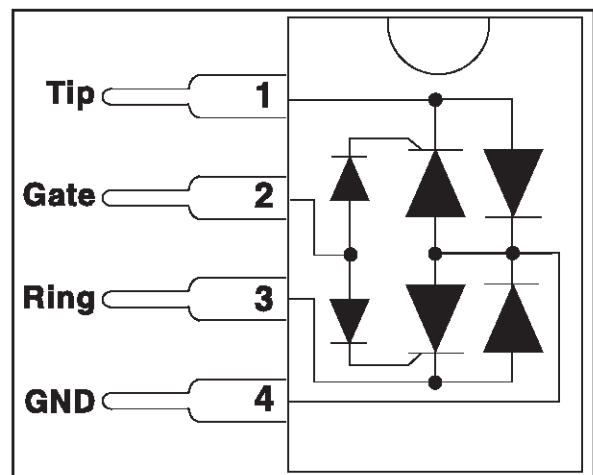
(*) with series resistors or PTC.

TM: ASD is trademarks of SGS-THOMSON Microelectronics.

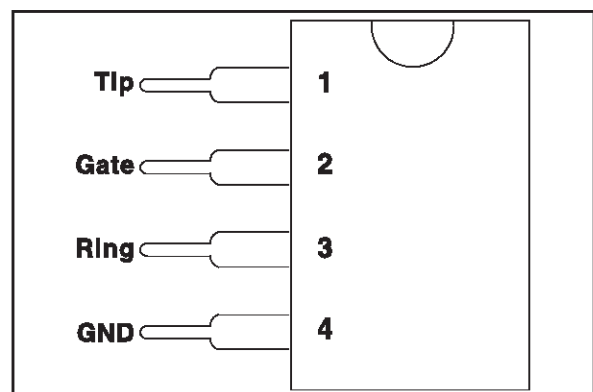
February 1998 - Ed: 3



SCHEMATIC DIAGRAM



CONNECTION DIAGRAM



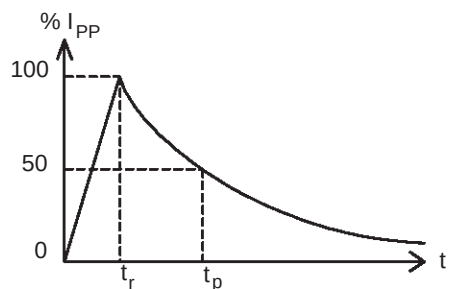
LCP150S

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25\text{ }^{\circ}\text{C}$)

Symbol	Parameter		Value	Unit
I_{PP}	Peak pulse current (see note 1)	10/1000 μs 5/320 μs 2/10 μs	50 60 150	A
I_{TSM}	Non repetitive surge peak on-state current F = 50 Hz	$t_p = 10\text{ ms}$ $t = 1\text{ s}$	25 8	A
I_{GSM}	Maximum gate current (half sine wave $t_p = 10\text{ ms}$)		2	A
V_{MLG} V_{MGL}	Maximum Voltage LINE/GND Maximum Voltage GATE/LINE		- 100 - 80	V
T_{stg} T_j	Storage temperature range Maximum operating junction temperature		- 55 to + 150 150	$^{\circ}\text{C}$ $^{\circ}\text{C}$
T_L	Maximum lead temperature for soldering during 10s		260	$^{\circ}\text{C}$

Note 1: Pulse waveform

10/1000 μs $t_r = 10\text{ }\mu\text{s}$ $t_p = 1000\text{ }\mu\text{s}$
 5/320 μs $t_r = 5\text{ }\mu\text{s}$ $t_p = 320\text{ }\mu\text{s}$
 2/10 μs $t_r = 2\text{ }\mu\text{s}$, $t_p = 10\text{ }\mu\text{s}$

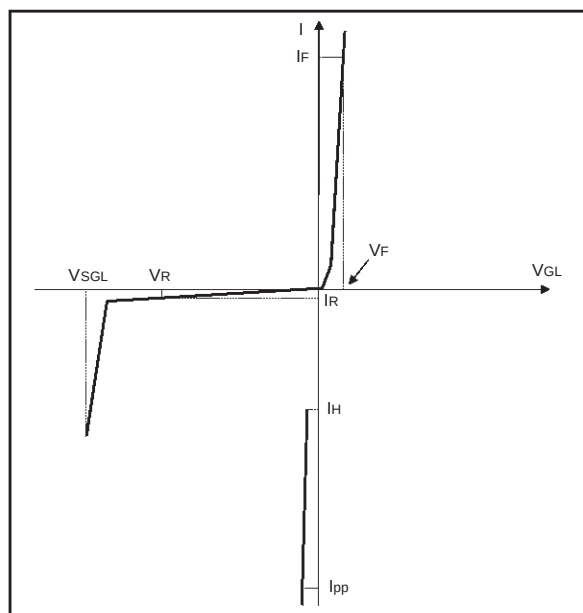


THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
$R_{th(j-a)}$	Junction-to-ambient	80	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified)

Symbol	Parameter
I_{GT}	Gate Trigger Current
I_H	Holding Current
I_R	Reverse Leakage Current LINE/GND
I_{RG}	Reverse Leakage Current GATE/LINE
V_R	Reverse Voltage LINE/GND
V_F	Forward Voltage LINE/GND
V_{GT}	Gate Trigger Voltage
V_{FP}	Peak Forward Voltage LINE/GND
V_{SGL}	Dynamic Switching Voltage GND/LINE
V_{gate}	GATE/GND Voltage
V_{LG}	LINE/GND Voltage
C	Off State Capacitance LINE/GND

**1 - PARAMETERS RELATED TO THE DIODE LINE/GND**

Symbol	Test Conditions	Max.	Unit
V_F	Square pulse, $T_p = 500 \mu\text{s}$, $I_F = 5 \text{ A}$	3	V
V_{FP}	$I_{pp} = 40 \text{ A}$, $10/1000 \mu\text{s}$.	15	V

2 - PARAMETERS RELATED TO PROTECTION THYRISTOR

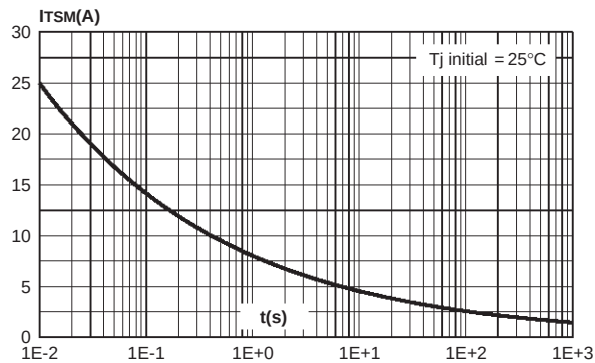
Symbol	Tests Conditions	Min.	Max.	Unit
I_{GT}	$V_{GND/LINE} = -48 \text{ V}$	0.2	15	mA
I_H	$V_{GATE} = -48 \text{ V}$ Note 2	150		mA
V_{GT}	at I_{GT}		2.5	V
I_{RG}	$T_c = 25^{\circ}\text{C}$ $V_{RG} = -75 \text{ V}$ $T_c = 70^{\circ}\text{C}$ $V_{RG} = -75 \text{ V}$		5 50	μA μA
V_{SGL}	$V_{GATE} = -48 \text{ V}$ Note 2		- 63	V

3 - PARAMETERS RELATIVE TO DIODE AND PROTECTION THYRISTOR

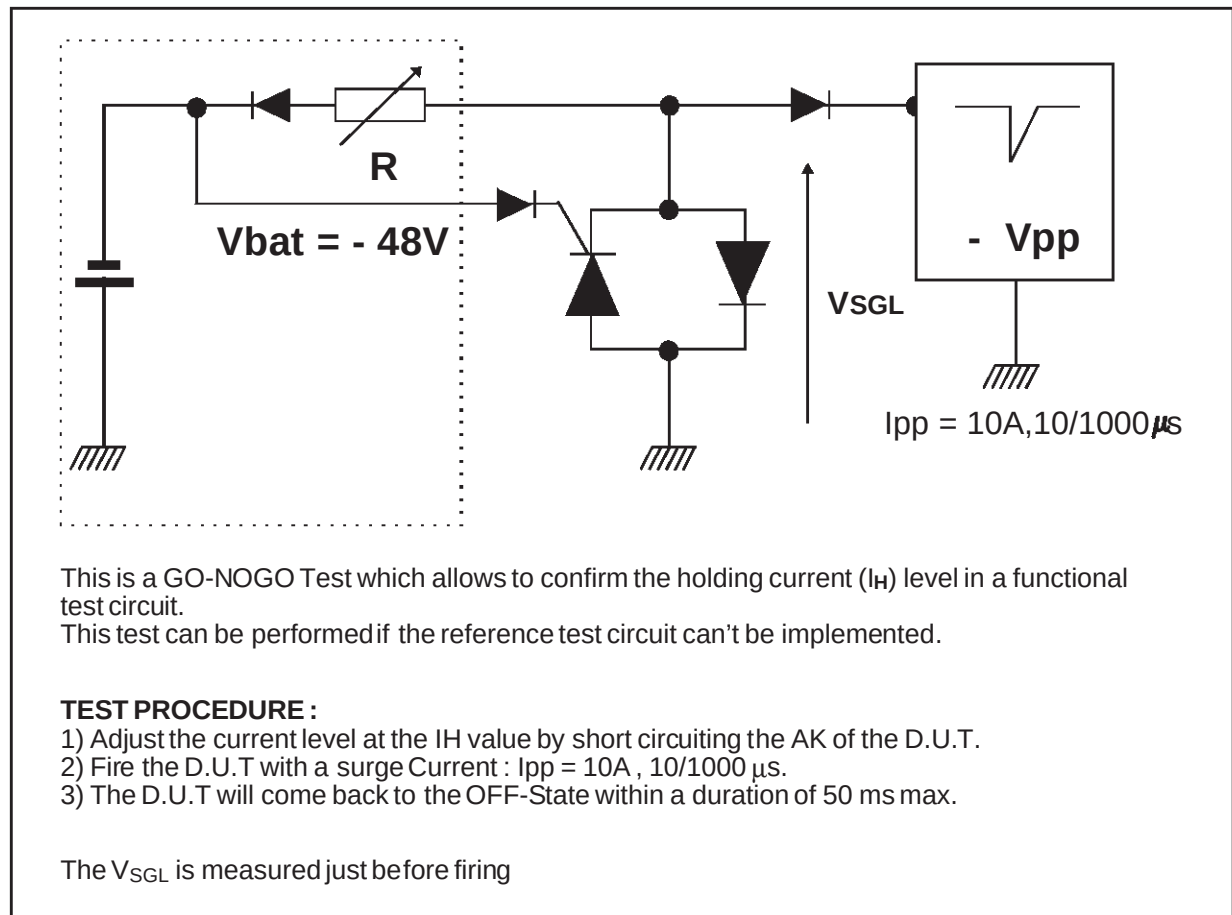
Symbol	Tests Conditions	Min.	Max.	Unit
I_R	$T_c = 25^{\circ}\text{C}$ $-1 < V_{GL} < -V_{bat}$ $V_R = -85 \text{ V}$ $T_c = 70^{\circ}\text{C}$ $-1 < V_{GL} < -V_{bat}$ $V_R = -85 \text{ V}$		5 50	μA μA
C	$V_R = -3 \text{ V}$ $F < 1\text{MHz}$ $V_R = -48 \text{ V}$ $F < 1\text{MHz}$		150 80	pF pF

Note 2 : See test circuit for I_H and V_{SGL} .

Fig. 1 : Surge peak current versus overload duration (typical values).

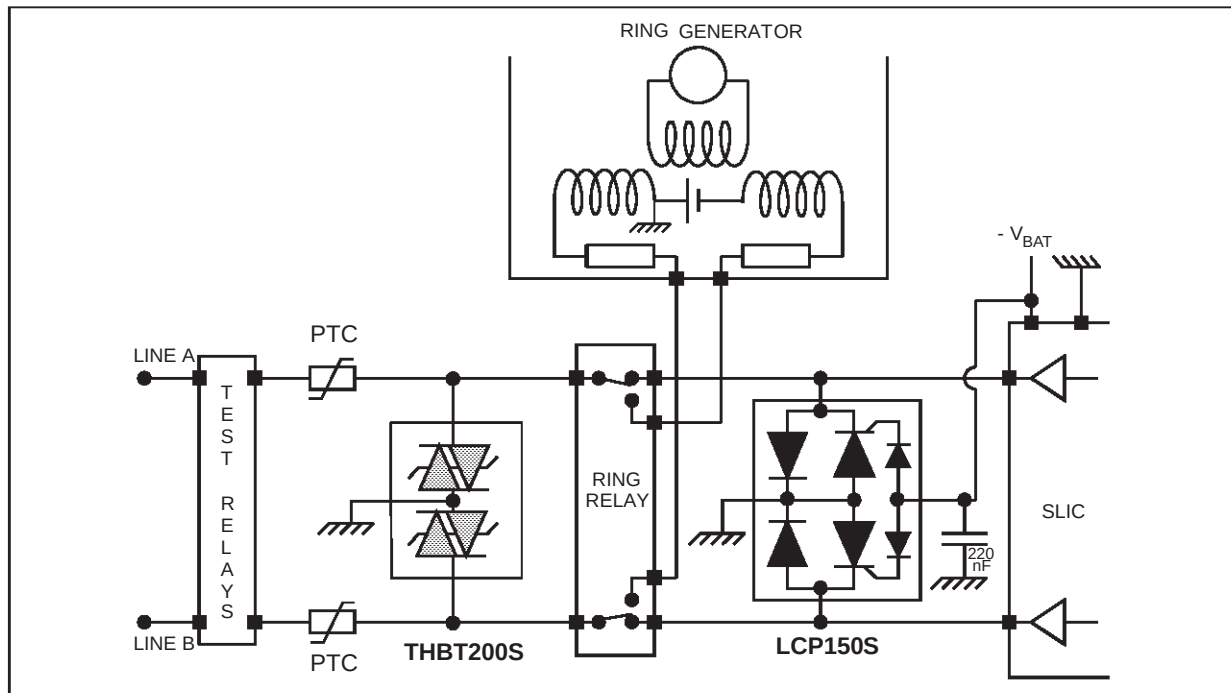


FUNCTIONAL HOLDING CURRENT (I_H) TEST CIRCUIT = GO - NOGO TEST.

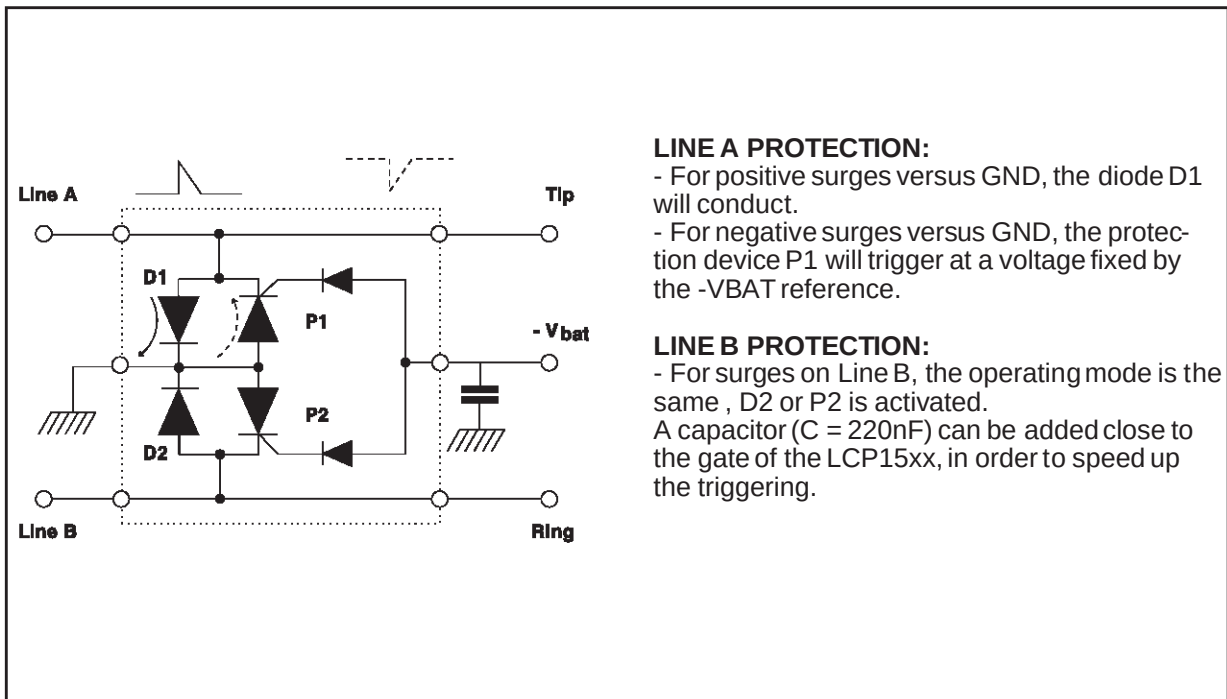


APPLICATION CIRCUIT

Typical SLIC Protection Concept.



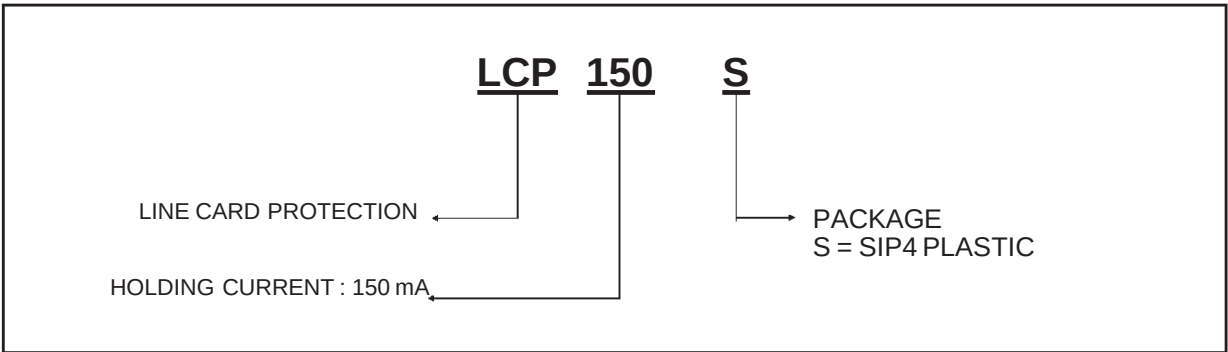
FUNCTIONAL DESCRIPTION



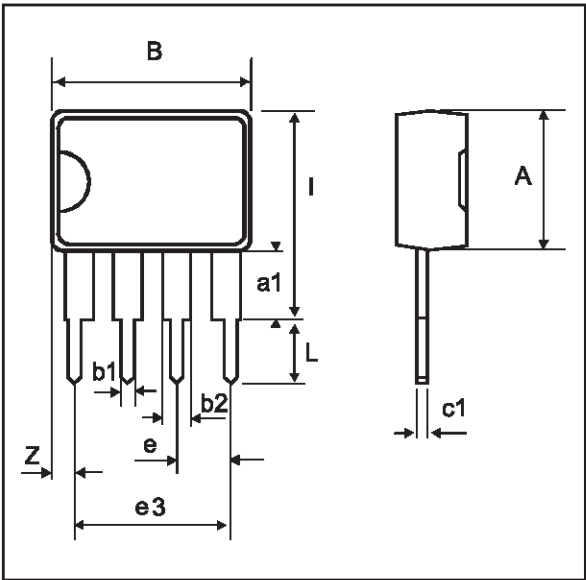
LCP150S

MARKING : Logo, Date Code, LCP150S.

ORDER CODE



PACKAGE MECHANICAL DATA
SIP 4



REF.	DIMENSIONS					
	Millimetres			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			7.10			0.280
a1	2.80			0.110		
B			10.15			0.400
b1		0.50			0.020	
b2	1.35		1.75	0.053		0.069
c1	0.38		0.50	0.015		0.020
e		2.54			0.100	
e3		7.62			0.200	
I			10.50			0.413
L		3.30			0.130	
Z			1.50			0.059

PACKAGING : Products supplied in antistatic tubes.

WEIGHT : 0.55g

Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectronics.

© 1998 SGS-THOMSON Microelectronics - Printed in Italy - All rights reserved.

SGS-THOMSON Microelectronics GROUP OF COMPANIES
Australia - Brazil - Canada - China - France - Germany - Italy - Japan - Korea - Malaysia - Malta - Morocco
The Netherlands - Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A.